

100V N-Channel Power MOSFET

DESCRIPTION

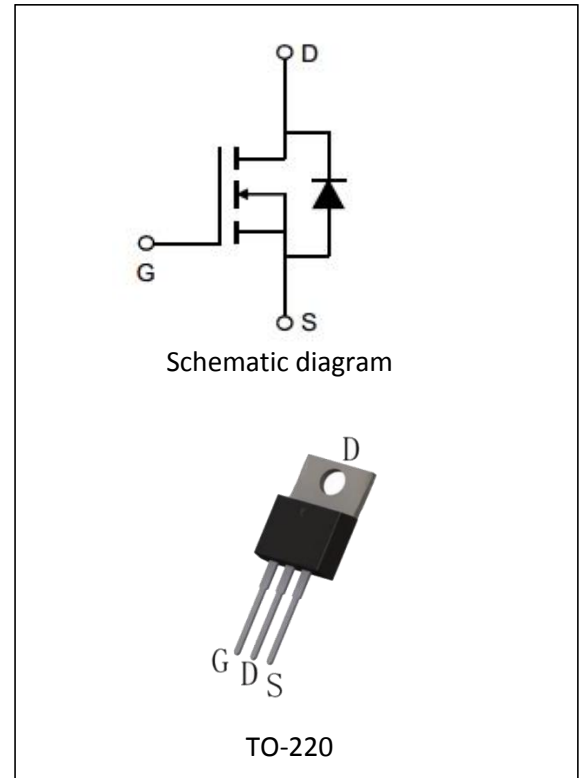
The IRFB4310 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. It can be used in a wide variety of applications.

KEY CHARACTERISTICS

- ① $V_{DS} = 100V, I_D = 110A$ $R_{DS(ON)} < 8m\Omega$ @ $V_{GS}=10V$
- ② Special process technology for high ESD capability
- ③ High density cell design for lower R_{dson}
- ④ Fully characterized avalanche voltage and current
- ⑤ Good stability and uniformity with high EAS
- ⑥ Excellent package for good heat dissipation

Application

- ① Power switching application
- ② Hard switched and High frequency circuits
- ③ Uninterruptible power supply



Package Marking And Ordering Information

Ordering Codes	Package	Product Code	Packing
IRFB4310	TO-220	MPG180N10P	Tube

Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	110	A
Drain Current-Pulsed ^(Note 1)	I_{DM}	440	A
Maximum Power Dissipation($T_c=25^\circ C$)	P_D	230	W
Single pulse avalanche energy ^(Note 2)	E_{AS}	600	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	$^\circ C$

Thermal Characteristic

Thermal Resistance,Junction-to-Case	$R_{\theta JC}$	0.63	$^\circ C/W$
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Electrical Characteristics (TA=25 °C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	100	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	2	3	4	V
Drain-Source On-State Resistance ^(Note 3)	R _{DS(ON)}	V _{GS} =10V, I _D =55A	-	8	11	mΩ
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} =25V, V _{GS} =0V, f=1.0MHz	-	8050	-	pF
Output Capacitance	C _{oss}		-	480	-	pF
Reverse Transfer Capacitance	C _{rss}		-	420	-	pF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =30V, I _D =50A, V _{GS} =10V, R _{GEN} =3Ω	-	25	-	nS
Turn-on Rise Time	t _r		-	24	-	nS
Turn-Off Delay Time	t _{d(off)}		-	90	-	nS
Turn-Off Fall Time	t _f		-	40	-	nS
Total Gate Charge	Q _g	V _{DS} =50V, I _D =55A V _{GS} =10V	-	160	-	nC
Gate-Source Charge	Q _{gs}		-	43	-	nC
Gate-Drain Charge	Q _{gd}		-	48	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =55A	-	-	1.2	V

Notes:

Repetitive Rating: Pulse width limited by maximum junction temperature.

EAS condition :T_j=25 °C, V_{DD}=50V, V_G=10V, L=0.5mH, R_g=25Ω

Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.

Guaranteed by design, not subject to production.

Characteristics Curves

Figure 1 Output Characteristics

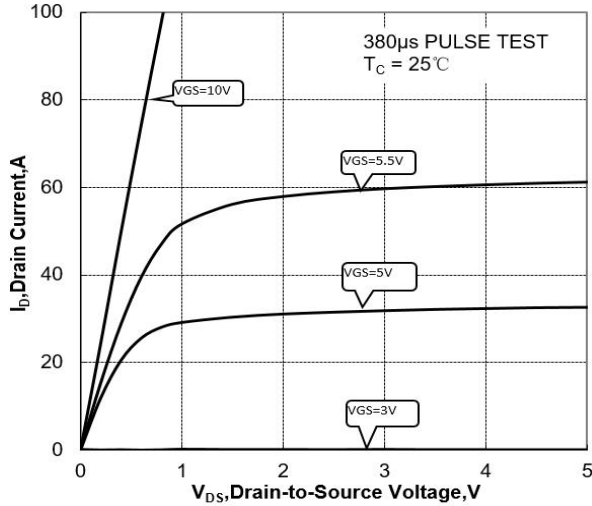


Figure 2 Transfer Characteristics

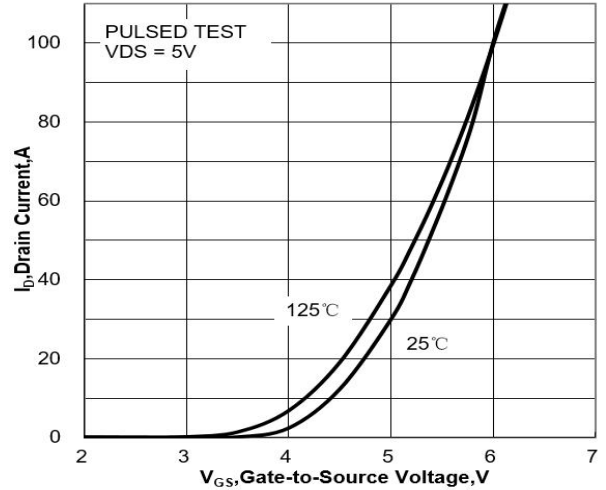


Figure 3 On-Resistance vs. ID and VGS

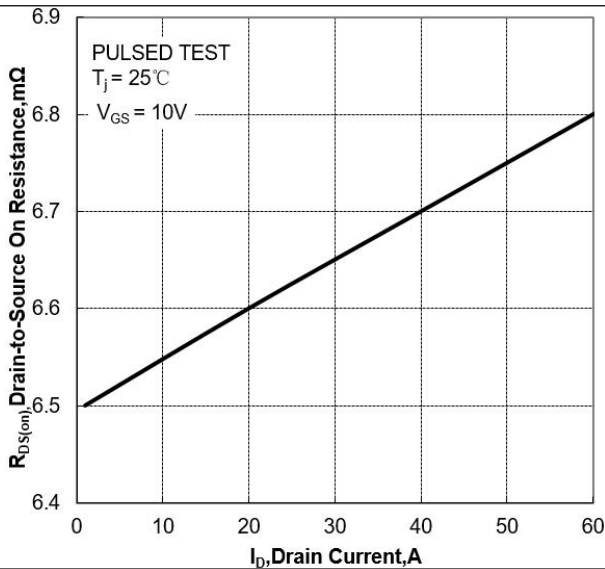


Figure 4 On-Resistance vs. Junction Temperature

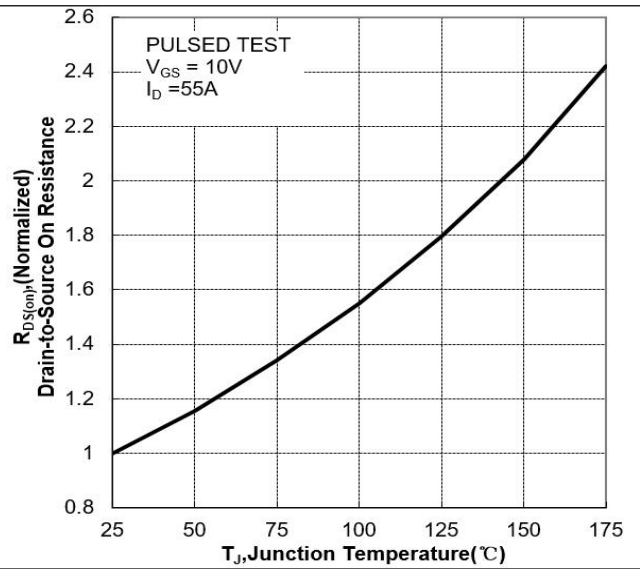


Figure 5 On-Resistance vs. VGS

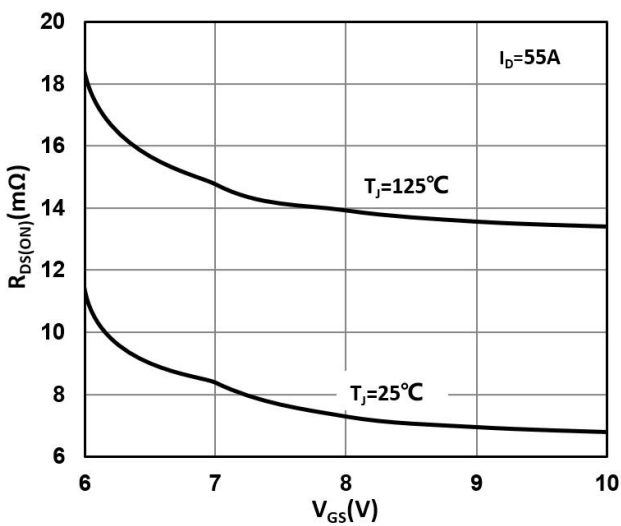


Figure 6 Body Diode Forward Voltage

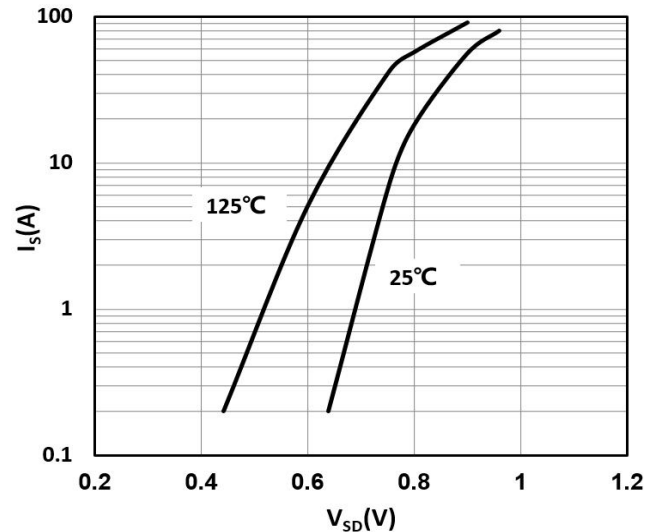


Figure 1 Output Characteristics

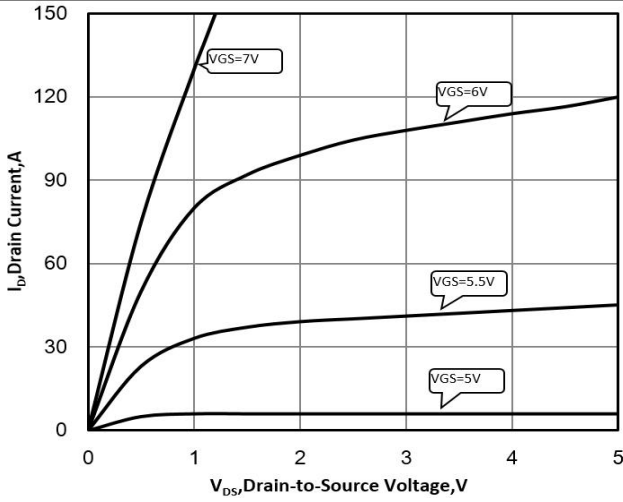


Figure 2 Transfer Characteristics

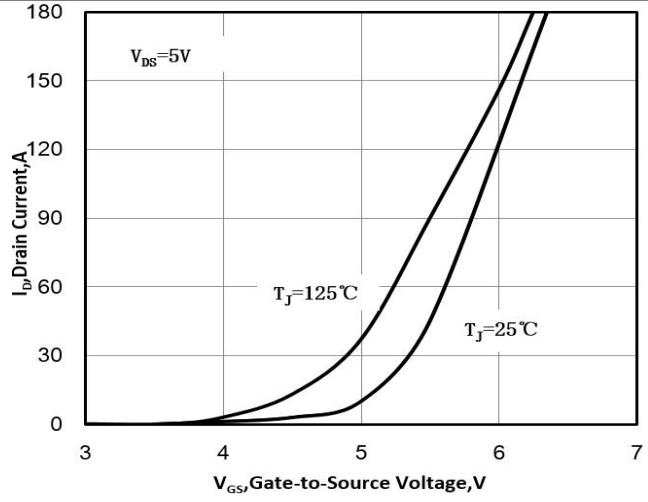


Figure 3 On-Resistance vs. ID and VGS

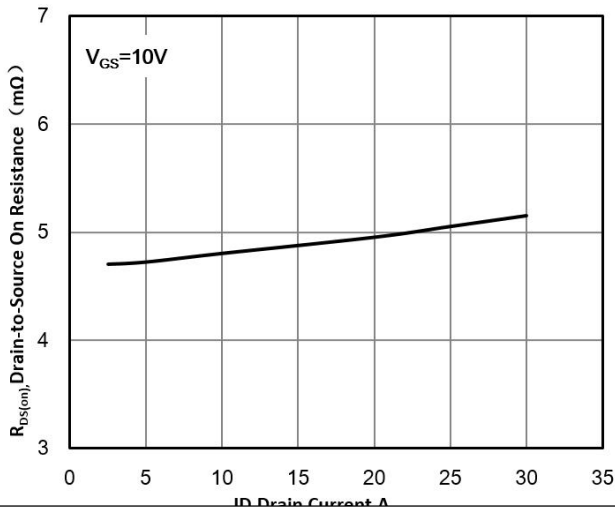


Figure 4 On-Resistance vs. Junction Temperature

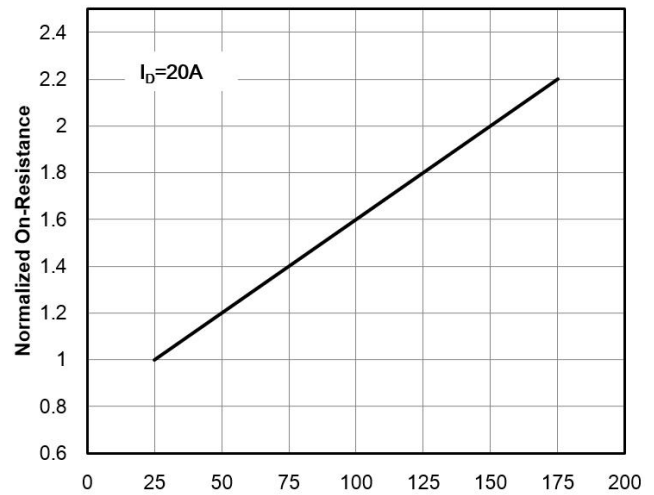


Figure 5 On-Resistance vs. VGS

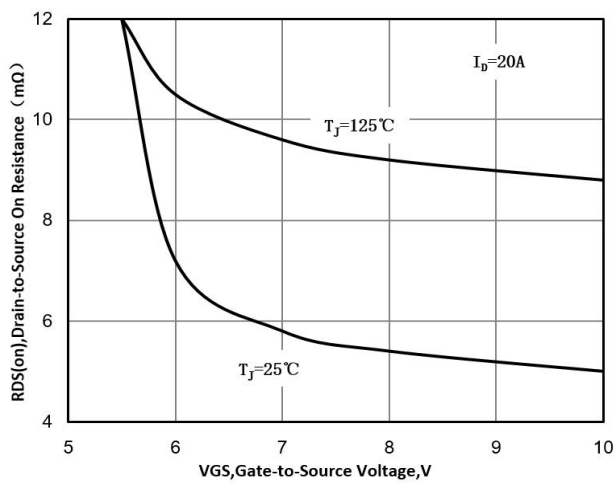


Figure 6 Body Diode Forward Voltage

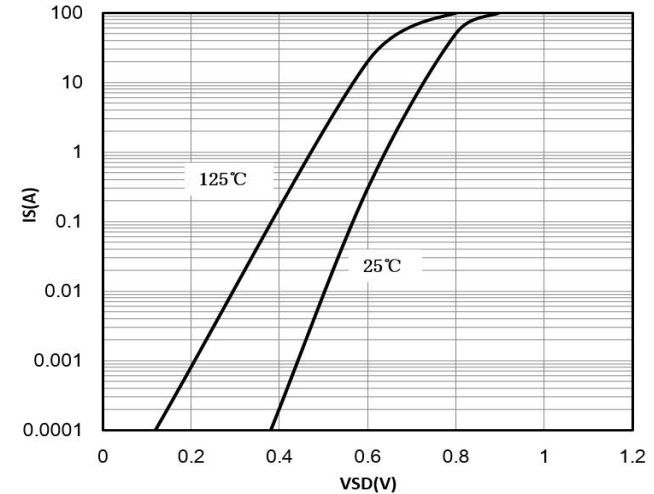


Figure 7 Gate-Charge Characteristics

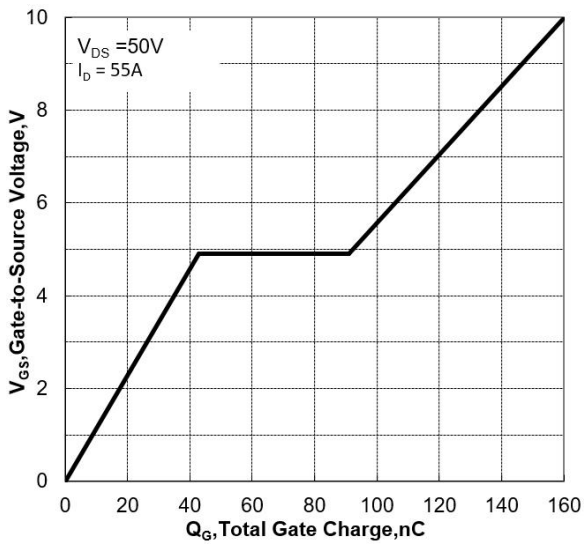


Figure 8 Capacitance Characteristics

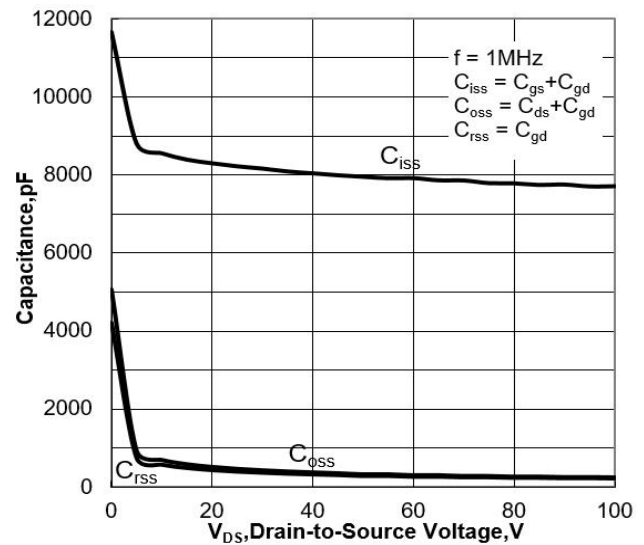


Figure 9 Maximum Forward Biased Safe Operation Area

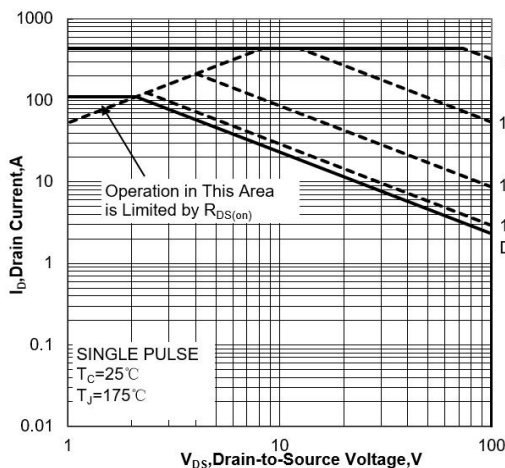


Figure 10 Single Pulse Power Rating Junction-to-Ambient

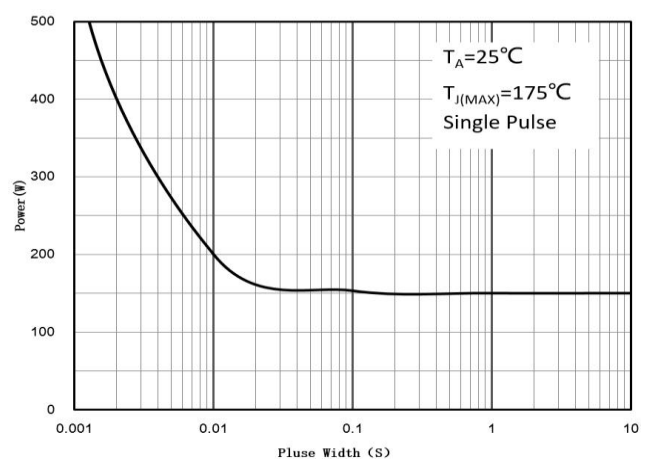
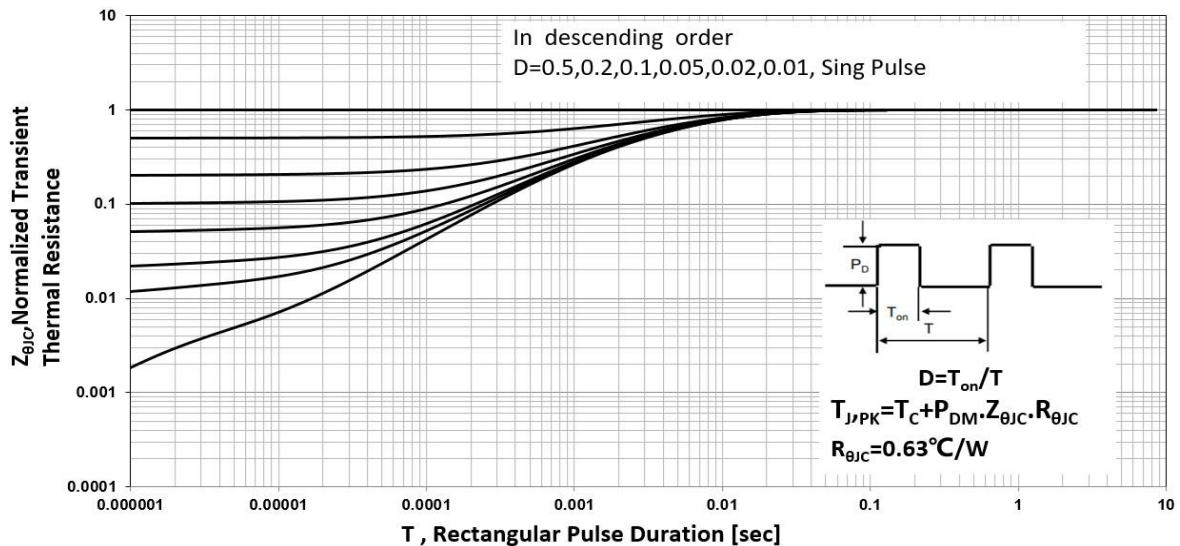
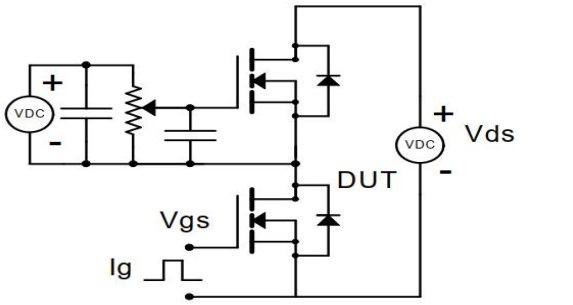
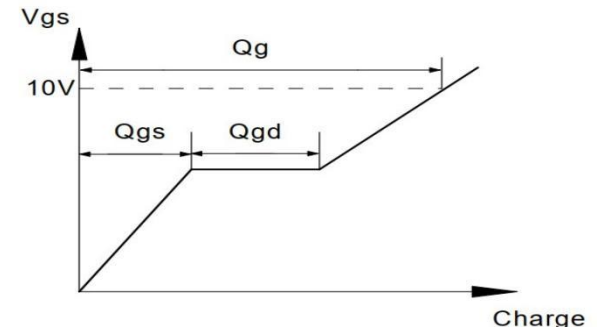
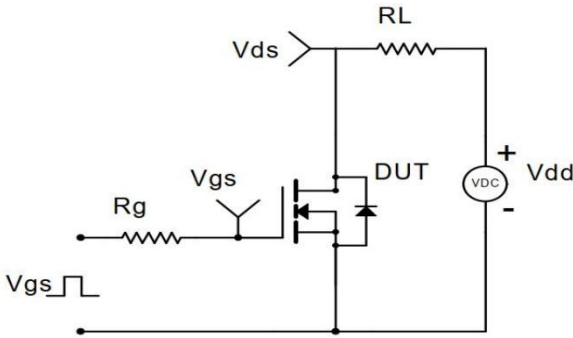
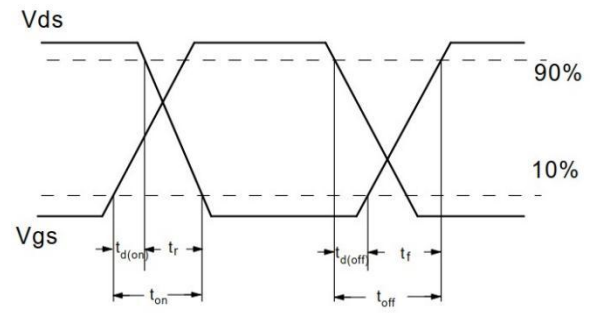
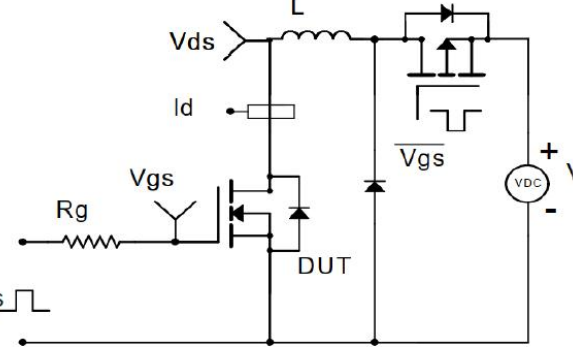
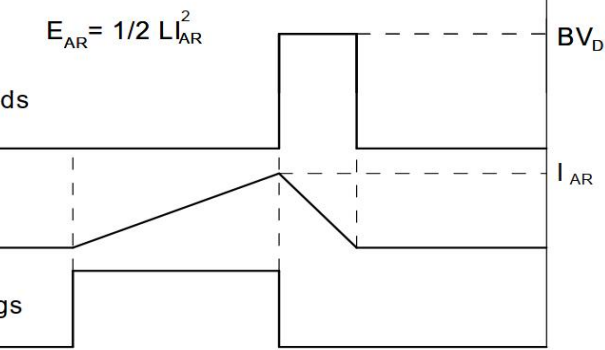
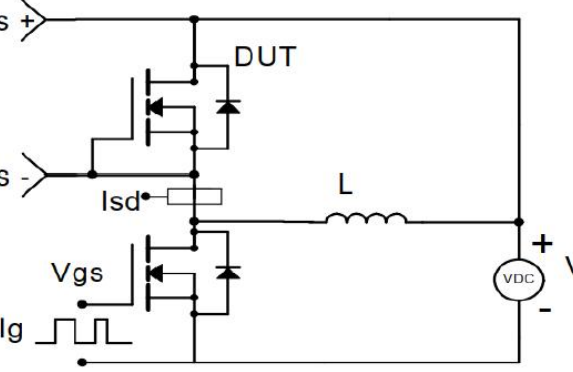
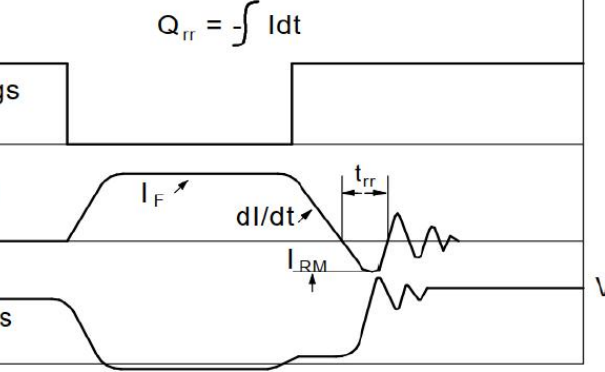


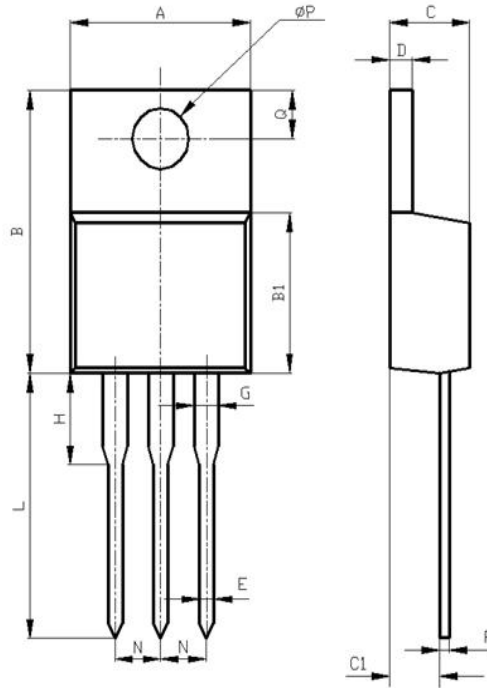
Figure 11 Normalized Maximum Transient Thermal Impedance



Test Circuit and Waveform

<p style="text-align: center;">Gate Charge Test Circuit</p> 	<p style="text-align: center;">Gate Charge Test Waveform</p> 
<p style="text-align: center;">Resistive Switching Test Circuit</p> 	<p style="text-align: center;">Resistive Switching Test Waveforms</p> 
<p style="text-align: center;">Unclamped Inductive Switching (UIS) Test Circuit</p> 	<p style="text-align: center;">Unclamped Inductive Switching (UIS) Test Waveforms</p> 
<p style="text-align: center;">Diode Recovery Test Circuit</p> 	<p style="text-align: center;">Diode Recovery Test Waveforms</p> 

Package Description



Items	Values(mm)	
	MIN	MAX
A	9.60	10.6
B	15.0	16.0
B1	8.90	9.50
C	4.30	4.80
C1	2.30	3.10
D	1.20	1.40
E	0.70	0.90
F	0.30	0.60
G	1.17	1.37
H	2.70	3.80
L	12.6	14.8
N	2.34	2.74
Q	2.40	3.00
Φ P	3.50	3.90

TO-220 package



NOTE:

1. Exceeding the maximum ratings of the device in performance may cause damage to the device, even the permanent failure, which may affect the dependability of the machine. Please do not exceed the absolute maximum ratings of the device when circuit designing.
2. When installing the heat sink, please pay attention to the torsional moment and the smoothness of the heat sink.
3. MOSFETs is the device which is sensitive to the static electricity, it is necessary to protect the device from being damaged by the static electricity when using it.
4. Shenzhen Minos reserves the right to make changes in this specification sheet and is subject to change without prior notice.

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